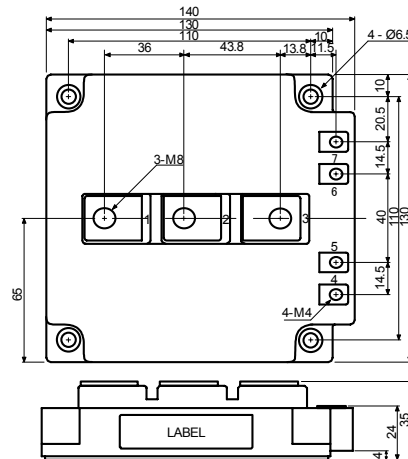
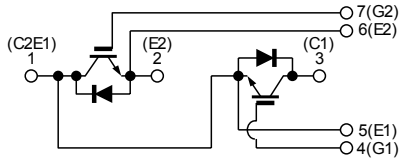


I G B T Module-Dual

6 0 0 A, 1 2 0 0 V

P D M B 6 0 0 B 1 2

□ 回路図 : *CIRCUIT*□ 外形寸法図 : *OUTLINE DRAWING*

Dimension: [mm]

□ 最大定格 : *MAXIMUM RATINGS* ($T_c = 25^\circ\text{C}$)

Item		Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage		V_{CES}	1, 200	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage		V_{GES}	± 20	V
コレクタ電流 Collector Current	DC	I_C	600	A
	1 ms	I_{CP}	1, 200	
コレクタ損失 Collector Power Dissipation		P_C	2, 800	W
接合温度 Junction Temperature Range		T_j	$-40 \sim +150$	$^\circ\text{C}$
保存温度 Storage Temperature Range		T_{stg}	$-40 \sim +125$	$^\circ\text{C}$
絶縁耐圧(Terminal to Base AC, 1 minute) Isolation Voltage		V_{ISO}	2, 500	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink		3 (30.6)	N · m (kgf · cm)
	Busbar to Main Terminal		M4 1.4 (14.3)	
			M8 10.5 (107)	

□ 電気的特性 : *ELECTRICAL CHARACTERISTICS* ($T_c = 25^\circ\text{C}$)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current		I_{CES}	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}$	—	—	12	mA
ゲート漏れ電流 Gate-Emitter Leakage Current		I_{GES}	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$	—	—	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 600\text{A}, V_{GE} = 15\text{V}$	—	1.9	2.4	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage		$V_{GE(th)}$	$V_{CE} = 5\text{V}, I_C = 600\text{mA}$	4	—	8	V
入力容量 Input Capacitance		C_{ies}	$V_{CE} = 10\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	—	50,000	—	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	t_r	$V_{CC} = 600\text{V}$ $R_L = 1\Omega$ $R_g = 1\Omega$ $V_{GE} = \pm 15\text{V}$	—	0.25	0.45	μs
	ターンオン時間 Turn-on Time	t_{on}		—	0.40	0.70	
	下降時間 Fall Time	t_f		—	0.25	0.35	
	ターンオフ時間 Turn-off Time	t_{off}		—	0.80	1.10	

□ フリーホイーリングダイオードの特性 : *FREE WHEELING DIODE RATINGS & CHARACTERISTICS* ($T_c = 25^\circ\text{C}$)

Item		Symbol	Rated Value	Unit
順電流 Forward Current	DC	I_F	600	A
	1 ms	I_{FM}	1, 200	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V_F	$I_F = 600\text{A}, V_{GE} = 0\text{V}$	—	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t_{rr}	$I_F = 600\text{A}, V_{GE} = -10\text{V}$ $di/dt = 1200\text{A}/\mu\text{s}$	—	0.25	0.35	μs

□ 熱的特性 : *THERMAL CHARACTERISTICS*

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	$R_{th(j-c)}$	Junction to Case	—	—	0.044	$^\circ\text{C}/\text{W}$
	Diode			—	—	0.085	

PDMB 600B12

Fig.1- Output Characteristics (Typical)

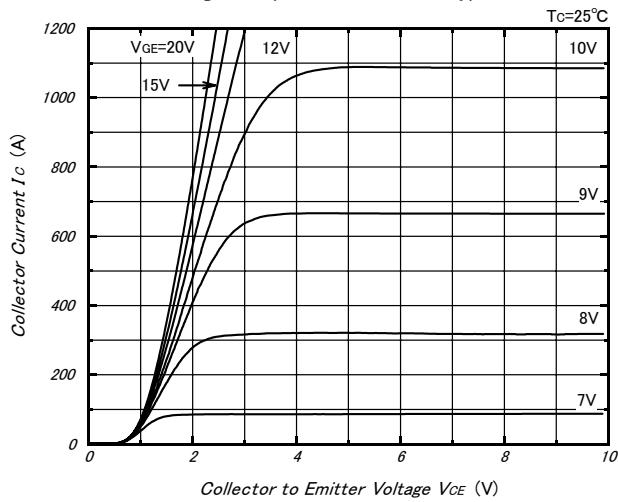


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

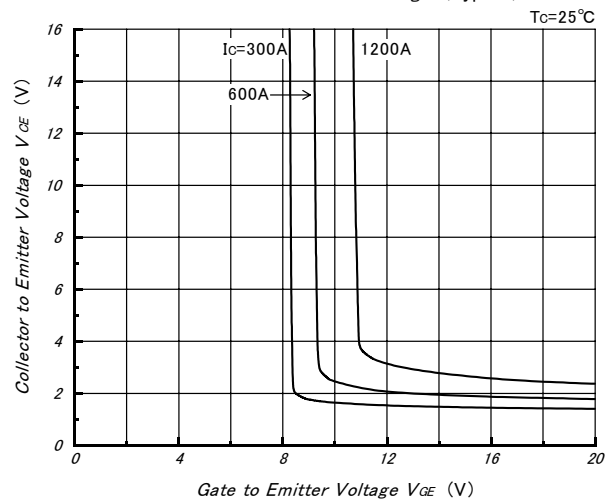


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

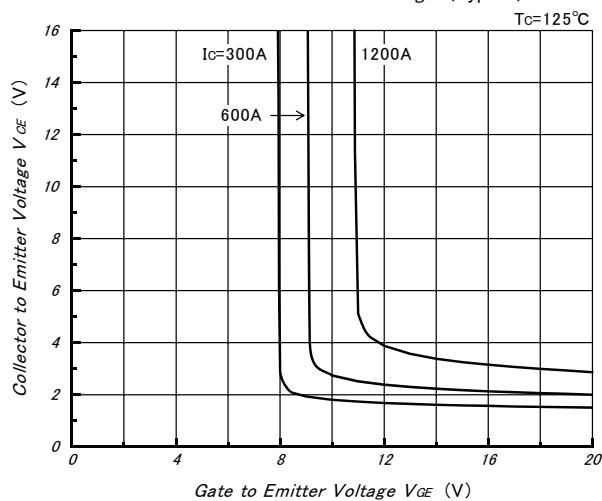


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

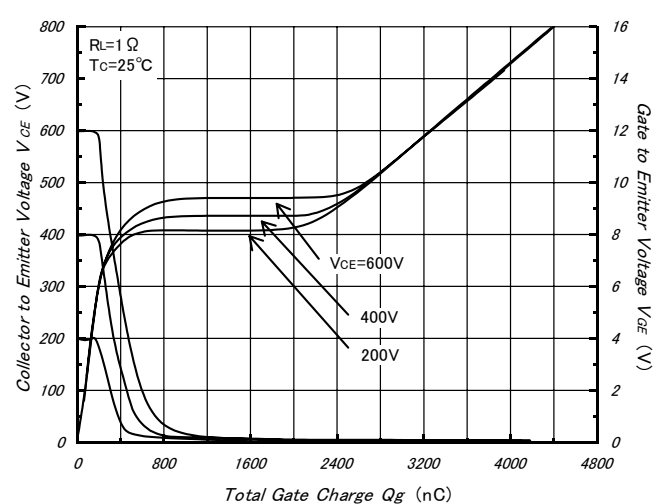


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

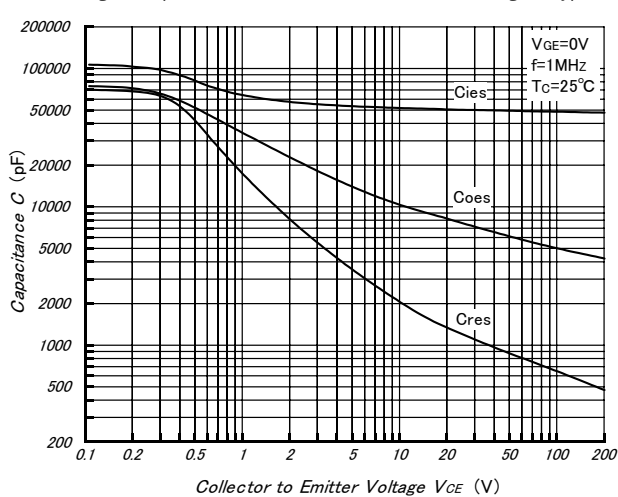
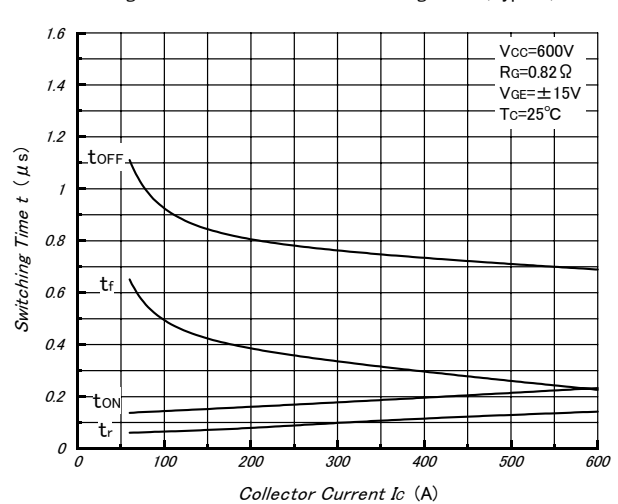


Fig.6- Collector Current vs. Switching Time (Typical)



PDMB 6 0 0 B 1 2

Fig.7- Series Gate Impedance vs. Switching Time (Typical)

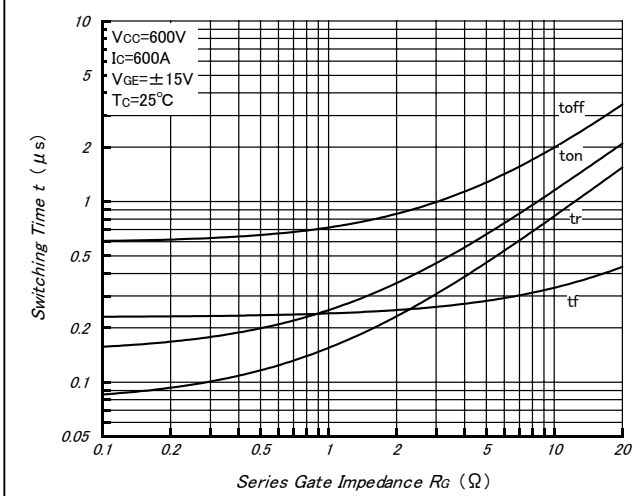


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

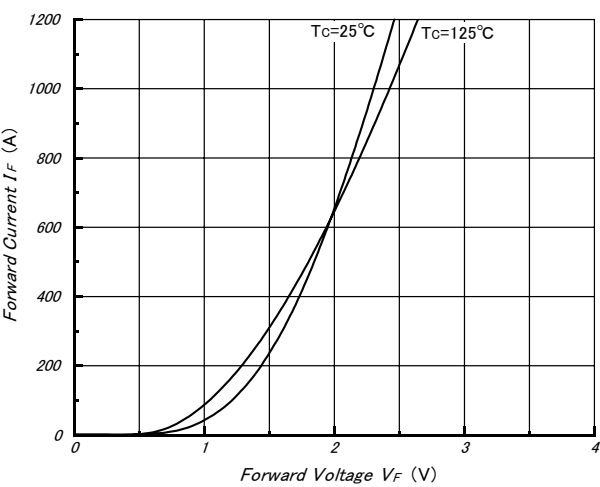


Fig.9- Reverse Recovery Characteristics (Typical)

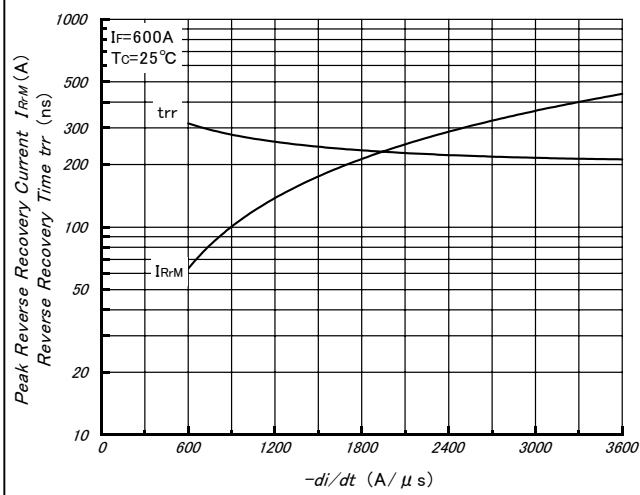


Fig.10- Reverse Bias Safe Operating Area

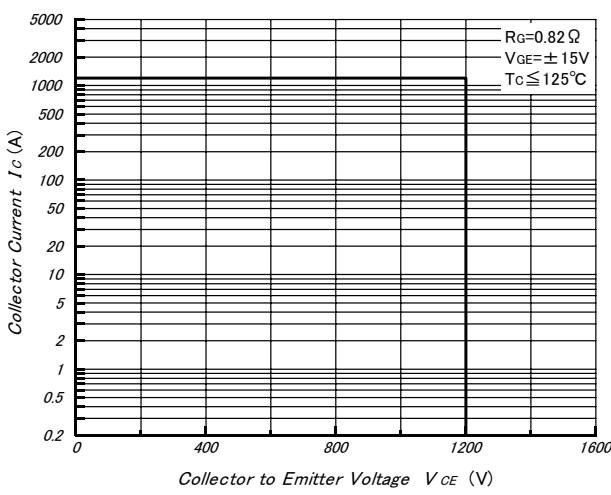


Fig.11- Transient Thermal Impedance

